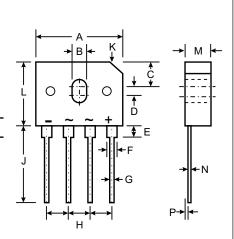


GBU10005 - GBU1010

SILICON BRIDGE RECTIFIERS 10.0A GLASS PASSIVATED BRIDGE RECTIFIER

Features

- Glass Passivated Die Construction
- High Case Dielectric Strength of 1500VRMS
- Low Reverse Leakage Current
- Surge Overload Rating to 220A Peak
- Ideal for Printed Circuit Board Applications
- Plastic Material: UL Flammability Classification Rating 94V-0



GBU							
Dim	Min	Max					
Α	21.8	22.3					
В	3.5	4.1					
С	7.4	7.9					
D	1.65	2.16					
E	2.25	2.75					
G	1.02	1.27					
Н	4.83	5.33					
J	17.5	18.0					
K	3.2 >	〈 45°					
L	18.3	18.8					
М	3.30	3.56					
N	0.46	0.56					
Р	0.76	1.0					
All Dimensions in mm							

Mechanical Data

Case: Molded Plastic

 Terminals: Plated Leads Solderable per MIL-STD-202, Method 208

Polarity: Marked on Body

Mounting: Through Hole for #6 Screw

Mounting Torque: 5.0 Inch-pounds Maximum

Marking: Date Code and Type Number

Weight: 6.6 grams (approx.)

Maximum Ratings and Electrical Characteristics @ TA = 25°C unless otherwise specified

Single phase, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	GBU 10005	GBU 1001	GBU 1002	GBU 1004	GBU 1006	GBU 1008	GBU 1010	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage		50	100	200	400	600	800	1000	V
RMS Reverse Voltage		35	70	140	280	420	560	700	V
Average Rectified Output Current (Note 1) @ T _C = 100°C		10							Α
Non-Repetitive Peak Forward Surge Current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)		220						А	
Forward Voltage (per element) @ I _F = 5.0A		1.0						V	
$ \begin{array}{cccccccccccccccccccccccccccccccccccc$		5.0 500						μА	
I ² t Rating for Fusing (Note 2)		200						A ² s	
Typical Junction Capacitance per Element (Note 3)		60						pF	
Typical Thermal Resistance Junction to Case (Note 1)		2.2						°C/W	
Operating and Storage Temperature Range		-55 to +150						°C	

Notes:

- 1. United mounted on 100 x 100 x 1.6mm copper plate heatsink.
- 2. Non-repetitive, for t > 1.0ms and < 8.3ms.
- 3. Measured at 1.0MHz and applied reverse voltage of 4.0V DC.

